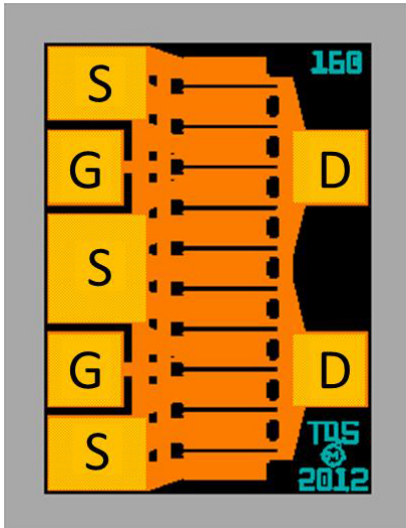


RFMW Introduces Discrete 1600-Micron FET from TriQuint Semiconductor

WDD Staff



[RFMW](#) [1] (San Jose, CA) has announced design and sales support for a discrete, 1600-Micron, GaAs pHEMT FET rated at 32.5dBm P1dB. TriQuint Semiconductor's TGF2160 is the latest addition to a family of high-efficiency FETs constructed without via holes thereby allowing for self-biasing and eliminating the need for a negative supply voltage. Designed using TriQuint's proven 0.25um pHEMT process which optimizes power and efficiency at high drain bias operating conditions. Applications include military, hi-rel defense and aerospace, test and measurement and commercial, broadband amplifiers up to K-band where high efficiency and linearity are required. Features include:

- 63% PAE at 8V and 517mA Idss.
- Silicon nitride, protective overcoat layer, providing environmental robustness and scratch protection.
- 0.41 x 0.54 x 0.10mm chip suitable for eutectic die attach.

For more information, visit www.rfmw.com [1].

Source URL (retrieved on 01/27/2015 - 4:40pm):

<http://www.wirelessdesignmag.com/product-releases/2013/07/rfmw-introduces-discrete-1600-micron-fet-triquint-semiconductor>

Links:

[1] <http://www.rfmw.com>